

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 100V$			400	μA
		$V_{GS} = 0V, V_{DS} = 80V$			2000	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 200A$		2.25	2.5	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 10\text{mA}$	2		4	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$			± 400	nA

Dynamic Characteristics

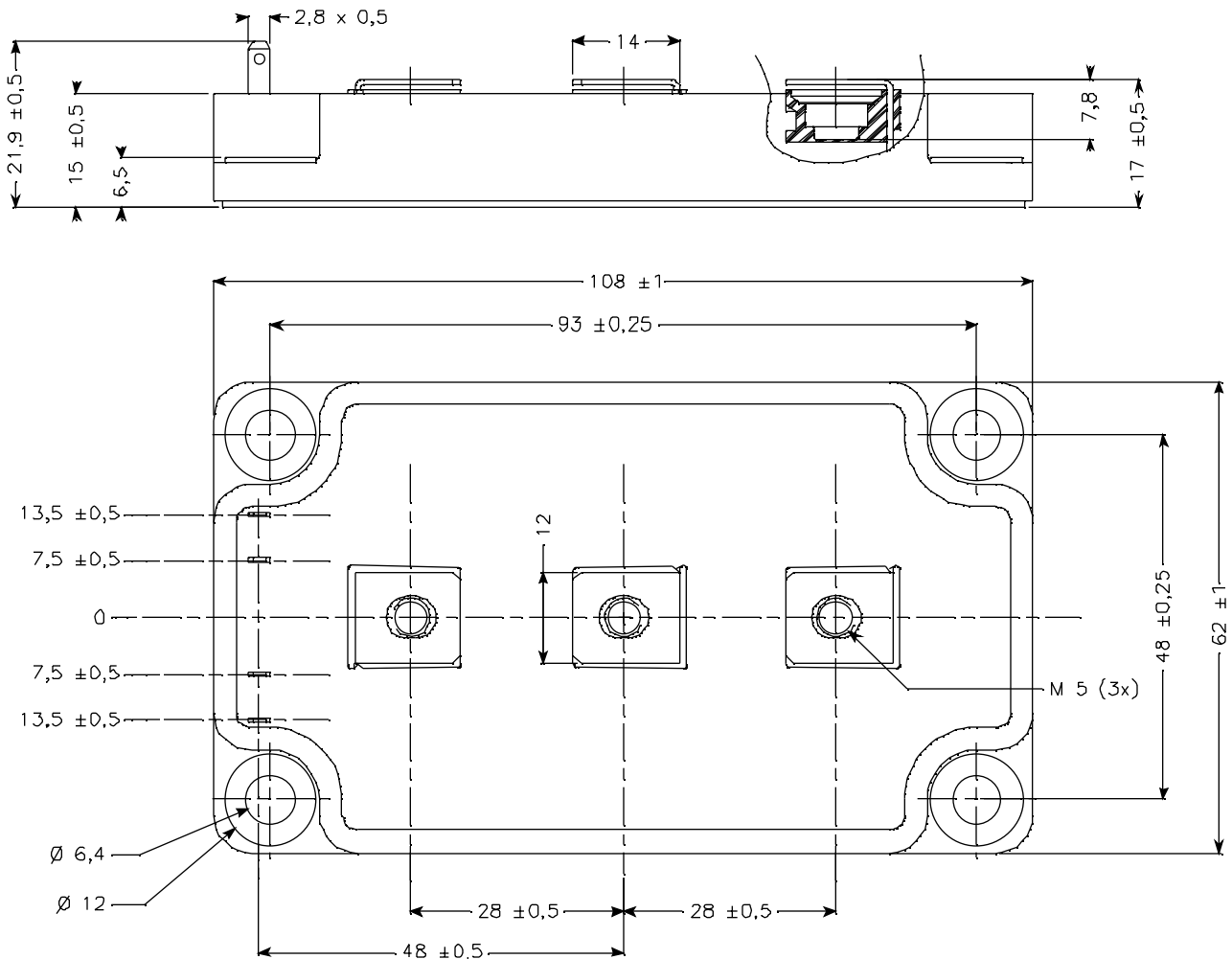
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$		40		nF
C_{oss}	Output Capacitance	$V_{DS} = 25V$		15.7		
C_{rss}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		5.9		
Q_g	Total gate Charge	$V_{GS} = 10V$ $V_{Bus} = 50V$ $I_D = 400A$		1360		nC
Q_{gs}	Gate – Source Charge			240		
Q_{gd}	Gate – Drain Charge			720		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C $V_{GS} = 15V$ $V_{Bus} = 66V$ $I_D = 400A$ $R_G = 1.25\Omega$		160		ns
T_r	Rise Time			240		
$T_{d(off)}$	Turn-off Delay Time			500		
T_f	Fall Time			160		
E_{on}	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 15V, V_{Bus} = 66V$ $I_D = 400A, R_G = 1.25\Omega$		2.2		mJ
E_{off}	Turn-off Switching Energy			2.41		
E_{on}	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15V, V_{Bus} = 66V$ $I_D = 400A, R_G = 1.25\Omega$		2.43		mJ
E_{off}	Turn-off Switching Energy			2.56		

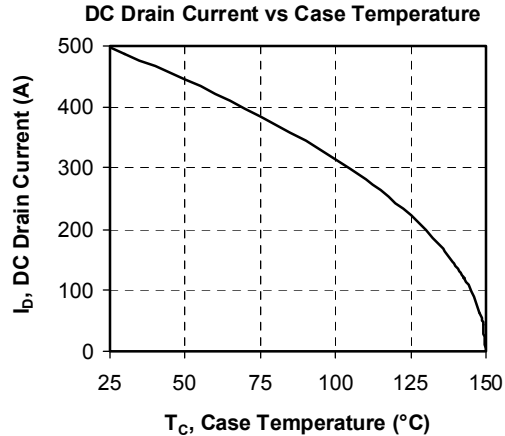
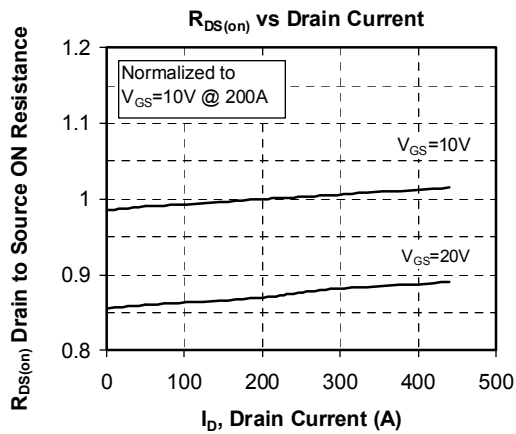
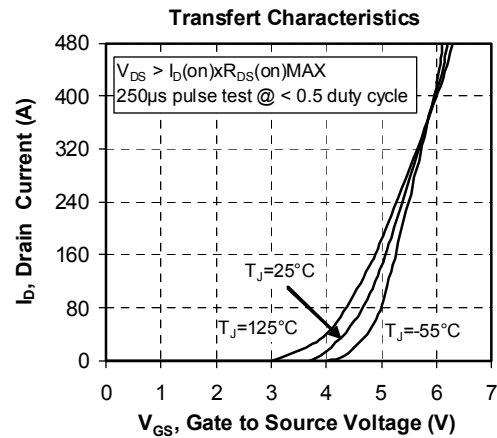
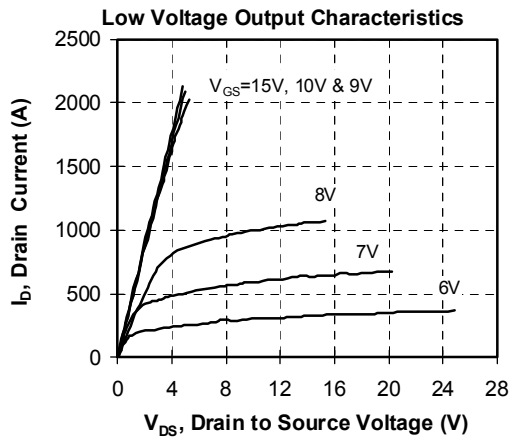
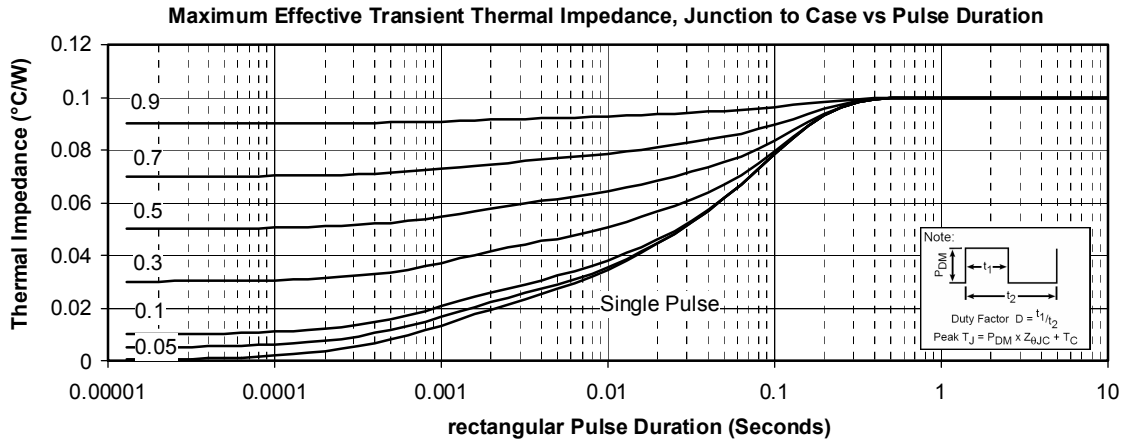
Chopper diode ratings and characteristics

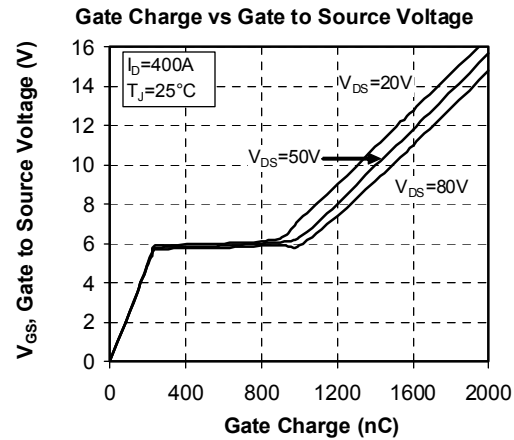
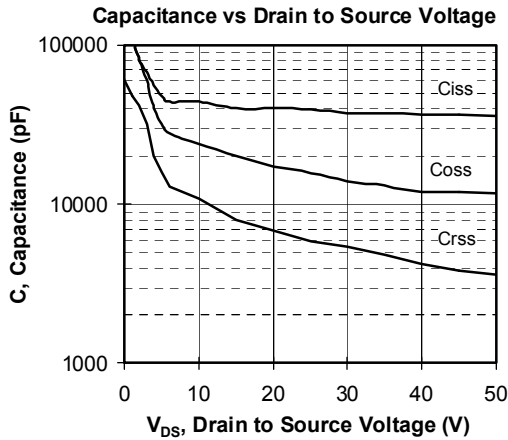
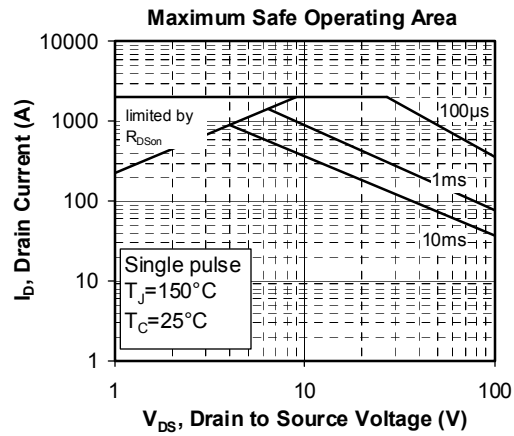
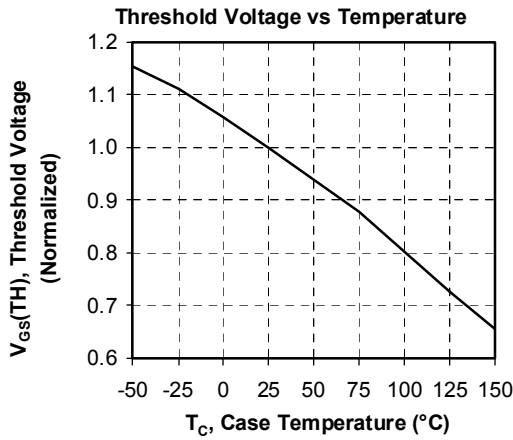
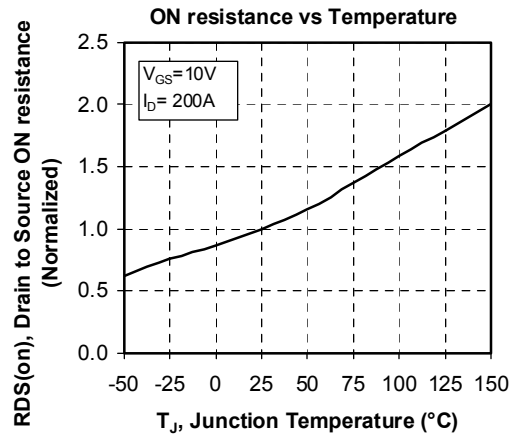
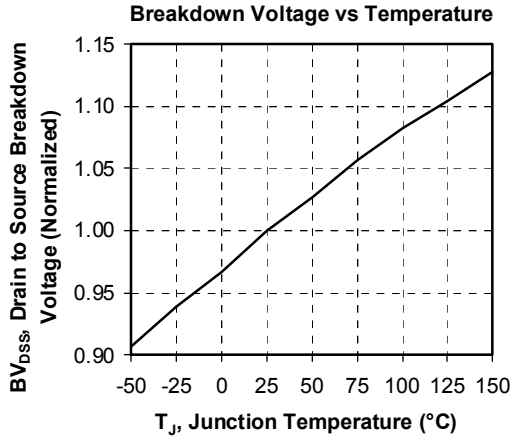
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		200			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 200V$	$T_j = 25^\circ\text{C}$		750	μA
			$T_j = 125^\circ\text{C}$		1000	
I_F	DC Forward Current	$T_c = 80^\circ\text{C}$		400		A
V_F	Diode Forward Voltage	$I_F = 400A$		1		V
		$I_F = 800A$		1.4		
		$I_F = 400A$	$T_j = 125^\circ\text{C}$		0.9	
t_{rr}	Reverse Recovery Time	$I_F = 400A$ $V_R = 133V$ $di/dt = 800A/\mu\text{s}$	$T_j = 25^\circ\text{C}$		60	ns
			$T_j = 125^\circ\text{C}$		110	
Q_{rr}	Reverse Recovery Charge	$I_F = 400A$ $V_R = 133V$ $di/dt = 800A/\mu\text{s}$	$T_j = 25^\circ\text{C}$		800	nC
			$T_j = 125^\circ\text{C}$		3360	

Thermal and package characteristics
Symbol Characteristic

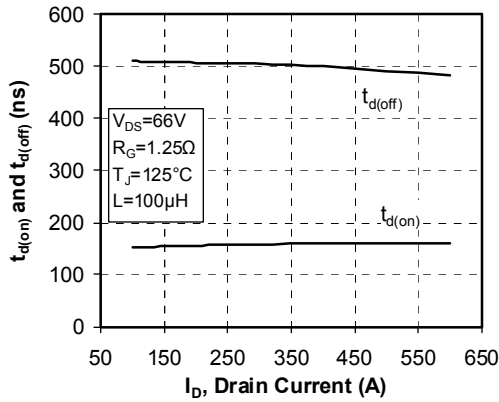
			<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
R_{thJC}	Junction to Case Thermal Resistance	Transistor			0.1	°C/W
		Diode			0.14	
V_{ISOL}	RMS Isolation Voltage, any terminal to case $t=1$ min, $I_{Isol}<1$ mA, 50/60Hz		2500			V
T_J	Operating junction temperature range		-40		150	°C
T_{STG}	Storage Temperature Range		-40		125	
T_C	Operating Case Temperature		-40		100	
Torque	Mounting torque	To heatsink	M6	3	5	N.m
		For terminals	M5	2	3.5	
Wt	Package Weight				280	g

SP6 Package outline (dimensions in mm)

 See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

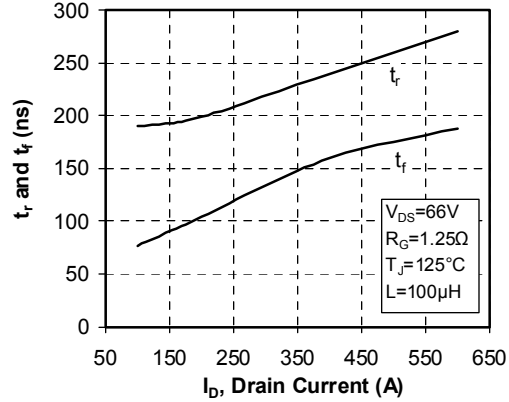
Typical Performance Curve




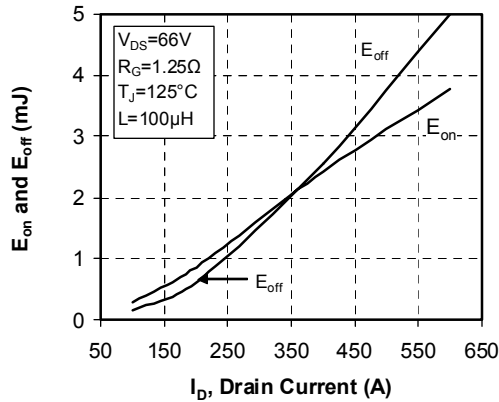
Delay Times vs Current



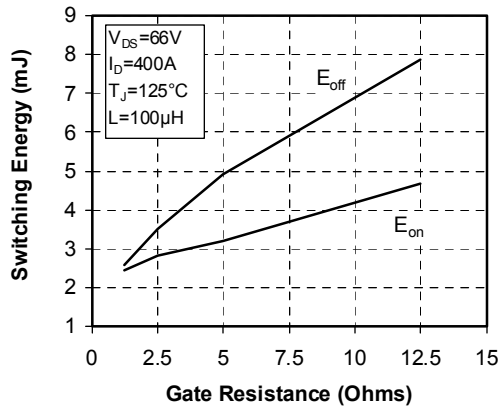
Rise and Fall times vs Current



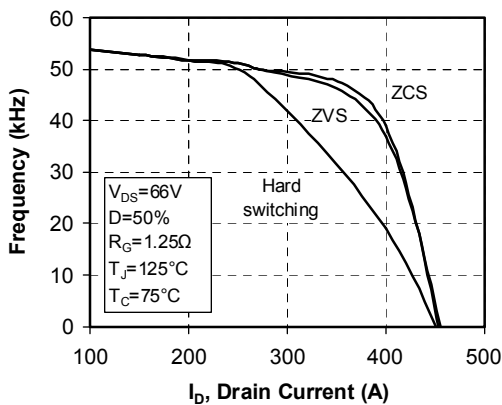
Switching Energy vs Current



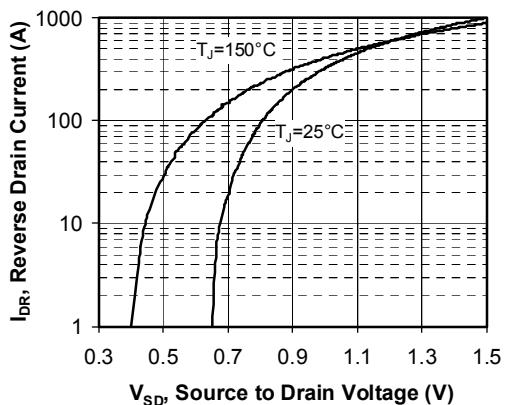
Switching Energy vs Gate Resistance



Operating Frequency vs Drain Current



Source to Drain Diode Forward Voltage



Microsemi reserves the right to change, without notice, the specifications and information contained herein

Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.